

AMENDMENTS to THE CLAIMS

1. (CURRENTLY AMENDED) A substrate comprising a first electrode,
and a second electrode being formed on an insulation film so
5 as to cover at least a part of said first electrode and electrically
connected with said first electrode through a contact hole formed
on said insulation film,

wherein

said first electrode includes a laminated structure of
10 a metal film and a protective film,

an etching rate of said metal film is almost equal to an
etching rate of said protective film with respect to a first
etching for forming said metal film and said protective film,

an etching rate of said protective film is almost zero
15 with respect to a second etching for forming said contact hole,

said protective film is an amorphous conductive oxide,
and

said amorphous conductive oxide is an oxide containing
indium oxide and zinc oxide.

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2. (CANCELED)

3. (CANCELED)

25 4. (ORIGINAL) The substrate according to Claim 1, wherein said
metal film contains molybdenum.

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5. (ORIGINAL) The substrate according to Claim 1, wherein said protective film is formed at a side of said contact hole with respect to said metal film.

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6. (ORIGINAL) The substrate according to Claim 1, wherein said metal film is formed at a side of said contact hole with respect to said protective film.

10 7. (ORIGINAL) The substrate according to Claim 1, further comprising a thin film transistor including said first electrode functioning as a drain electrode, a source electrode and a gate electrode,

15 wherein said second electrode functions as a pixel electrode controlled by said thin film transistor.

8. (ORIGINAL) The substrate according to Claim 7, further comprising

20 a gate signal line being branched from said gate electrode of said thin film transistor and

a gate insulation film covering at least parts of said gate electrode,

wherein said drain electrode of said thin film transistor is formed on said gate insulation film, and

25 said protective film protects said gate insulation film under said drain electrode from said second etching.

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9. (ORIGINAL) A liquid crystal display device comprising,
the substrate according to Claim 1,

a counter substrate opposed to said substrate, and

5 a liquid crystal inserted between said substrate and said
counter substrate.

10. (CURRENTLY AMENDED) A manufacturing method of a substrate
comprising,

10 a process for forming a first electrode,

a process for forming an insulation film covering at least
a part of said first electrode,

a process for forming a contact hole in said insulation
film by removing a part of said insulation film, and

15 a process for forming a second electrode on said insulation
film where said first electrode and said second electrode are
electrically connected through said contact hole,

wherein

said process for forming the first electrode comprises,

20 a process for laminating a metal film and a protective
film where said protective film is an amorphous conductive oxide
and said amorphous conductive oxide is an oxide containing indium
oxide and zinc oxide, and

a process for patterning both of said laminated metal film
25 and protective film by a first etching where an etching rate
of said metal film is almost equal to an etching rate of said

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protective film, and

 said process for forming the contact hole comprises,
 a process for forming said contact hole in said insulation
film by a second etching where an etching rate of said protective
5 film is almost zero.

11. (ORIGINAL) The manufacturing method of the substrate
according to Claim 10,

 wherein said process for patterning comprises a process
10 for patterning said metal film and said protective film by
wet-etching using a mixed solution of weak acid.

12. (ORIGINAL) The manufacturing method of the substrate
according to Claim 10 where said first electrode functions as
15 a drain electrode of a thin film transistor, and said second
electrode functions as a pixel electrode controlled by said thin
film transistor, the method further comprising,

 a process for forming a gate signal line,

 a process for forming a gate electrode of said thin film
20 transistor where said gate electrode is branched from said gate
signal line,

 a process for forming a gate insulation film covering at
least a part of said gate signal line,

 a process for forming a source signal line,

25 a process for forming a source electrode of said thin film
transistor where said source electrode is branched from said

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source signal line, and

a process for removing a part of said gate insulation film
on said gate signal line,

wherein

5 said second etching is a dry-etching, and a part of said
gate insulation film is removed while forming said contact hole
by said dry-etching.

13. (CANCELED)

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14. (CANCELED)

15. (ORIGINAL) The substrate according to Claim 10, wherein said
metal film contain molybdenum.

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